

6N90

Power MOSFET

6.2A, 900V N-CHANNEL POWER MOSFET

■ DESCRIPTION

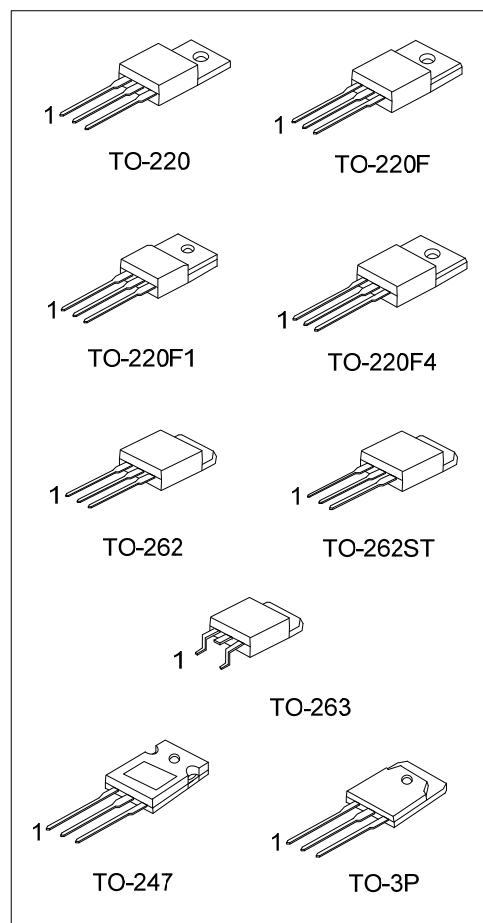
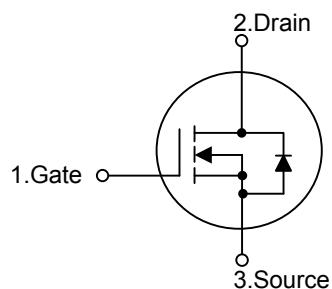
The UTC **6N90** is a N-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **6N90** is generally applied in high efficiency switch mode power supplies.

■ FEATURES

- * $R_{DS(ON)} \leq 1.75 \Omega$ @ $V_{GS}=10V$, $I_D=3.1A$
- * Fast switching
- * 100% avalanche tested
- * Improved dv/dt capability

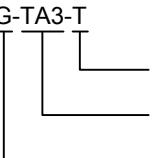
■ SYMBOL



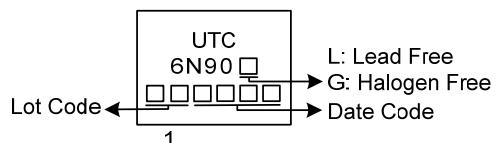
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N90L-TA3-T	6N90G-TA3-T	TO-220	G	D	S	Tube
6N90L-TF3-T	6N90G-TF3-T	TO-220F	G	D	S	Tube
6N90L-TF1-T	6N90G-TF1-T	TO-220F1	G	D	S	Tube
6N90L-TF34-T	6N90G-TF34-T	TO-220F4	G	D	S	Tube
6N90L-T2Q-T	6N90G-T2Q-T	TO-262	G	D	S	Tube
6N90L-T2ST-T	6N90G-T2ST-T	TO-262ST	G	D	S	Tube
6N90L-TQ2-T	6N90G-TQ2-T	TO-263	G	D	S	Tube
6N90L-TQ2-R	6N90G-TQ2-R	TO-263	G	D	S	Tape Reel
6N90L-T3P-T	6N90G-T3P-T	TO-3P	G	D	S	Tube
6N90L-T47-T	6N90G-T47-T	TO-247	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

 6N90G-TA3-T	(1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1 TF34: TO-220F4, T2Q: TO-262, T2ST: TO-262ST, TQ2: TO-263, T3P: TO-3P, T47: TO-247 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	900	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous ($T_c=25^\circ\text{C}$)	I_D	6.2	A
	Pulsed (Note 2)	I_{DM}	24	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	65	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220/TO-262	P_D	140	W
	TO-262ST/TO-263		36	W
	TO-220F/TO220F1		230	W
	TO-220F4		220	W
	TO-3P		+150	$^\circ\text{C}$
	TO-247		-55 ~ +150	$^\circ\text{C}$
Junction Temperature		T_J		
Storage Temperature		T_{STG}		

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 10\text{mH}$, $I_{AS} = 3.6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 6.0\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO220F1/TO-220F4			
	TO-262/TO-262ST			
Junction to Case	TO-263			
	TO-3P		40	$^\circ\text{C/W}$
	TO-247		50	$^\circ\text{C/W}$
	TO-220/TO-262	θ_{JC}	0.89	$^\circ\text{C/W}$
	TO-262ST/TO-263			
Junction to Case	TO-220F/TO220F1		3.47	$^\circ\text{C/W}$
	TO-220F4			
	TO-3P		0.54	$^\circ\text{C/W}$
	TO-247		0.57	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise specified)

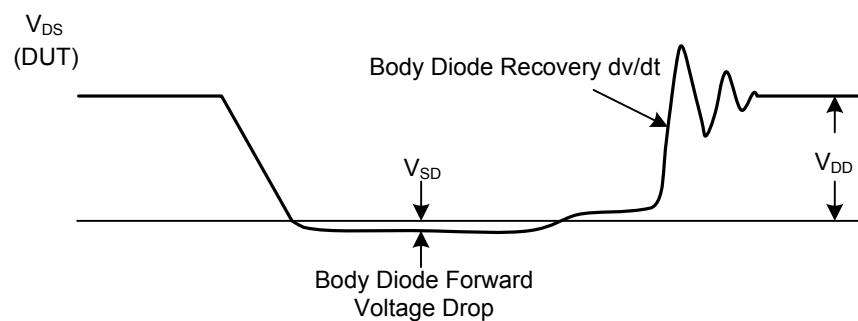
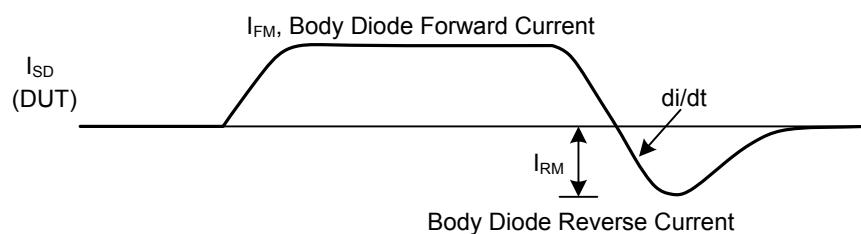
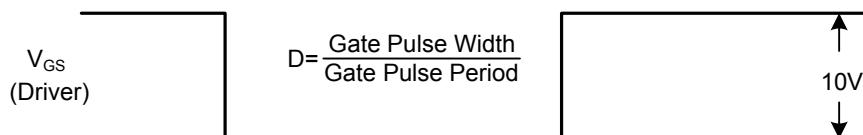
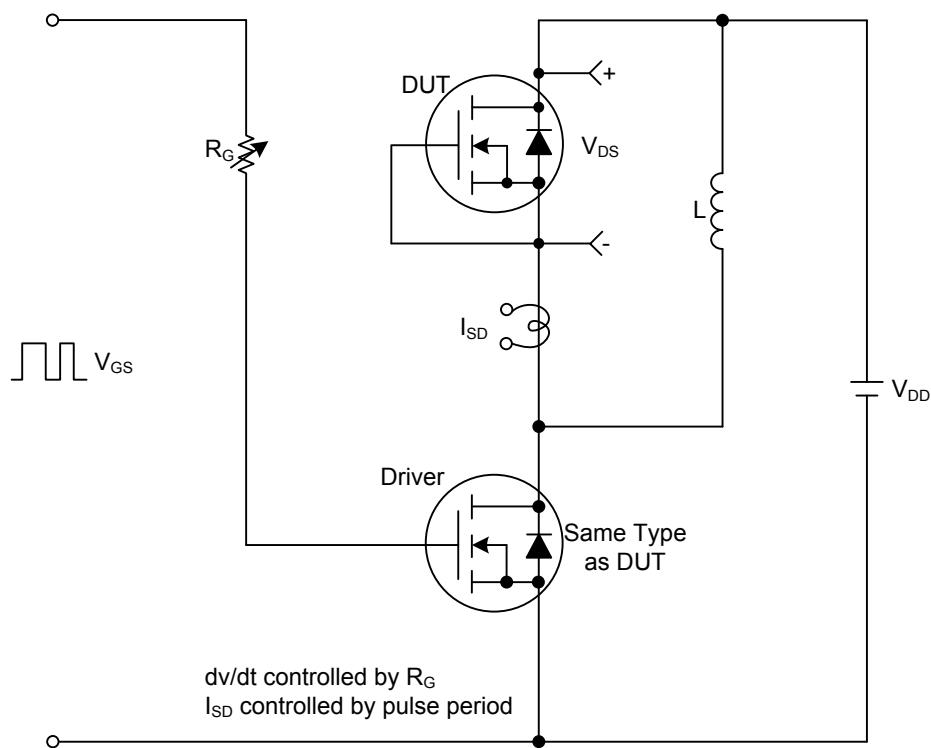
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	900			V
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=900\text{V}, V_{GS}=0\text{V}$		10		μA
Gate- Source Leakage Current	Forward	$V_{GS}=+30\text{V}, V_{DS}=0\text{V}$			+100	nA
	Reverse	$V_{GS}=-30\text{V}, V_{DS}=0\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	3.0		5.0	V
Static Drain-Source On-State Resistance	$R_{DS(\text{ON})}$	$V_{GS}=10\text{V}, I_D=3.1\text{A}$			1.75	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1.0\text{MHz}$		1330		pF
Output Capacitance	C_{OSS}			140		pF
Reverse Transfer Capacitance	C_{RSS}			14		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1, 2)	Q_G	$V_{DS}=720\text{V}, V_{GS}=10\text{V}, I_D=6.0\text{A}$ $I_G=1\text{mA}$ (Note 1, 2)		50		nC
Gate to Source Charge	Q_{GS}			15		nC
Gate to Drain Charge	Q_{GD}			17		nC
Turn-ON Delay Time (Note 1, 2)	$t_{D(\text{ON})}$	$V_{DD}=100\text{V}, V_{GS}=10\text{V}, I_D=6.0\text{A}, R_G=25\Omega$ (Note 1, 2)		25		ns
Rise Time	t_R			22		ns
Turn-OFF Delay Time	$t_{D(\text{OFF})}$			100		ns
Fall-Time	t_F			45		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Continuous Drain-Source Diode Forward Current	I_S				6.0	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				24	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=6.2\text{A}, V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	t_{rr}	$I_S=6.2\text{A}, V_{GS}=0\text{V}, \frac{dI_F}{dt}=100\text{A}/\mu\text{s}$ (Note 1)		670		ns
Body Diode Reverse Recovery Charge	Q_{rr}			5.5		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$.

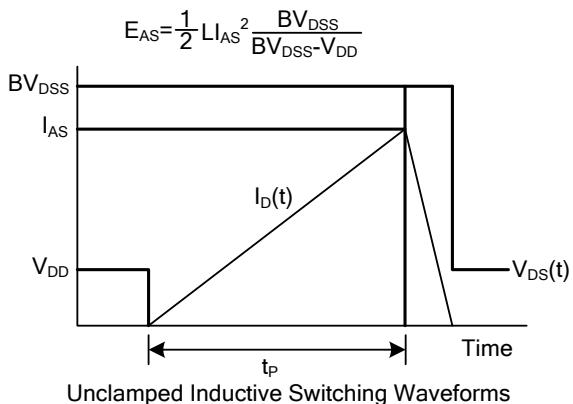
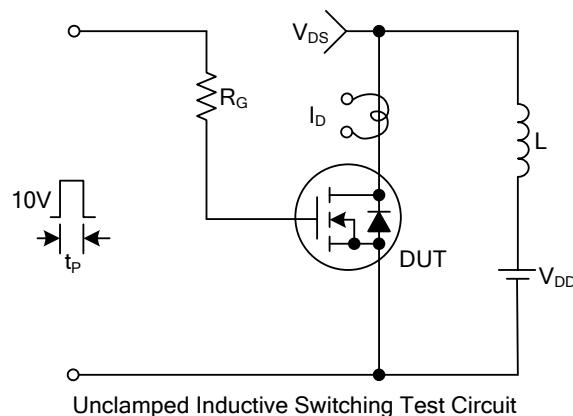
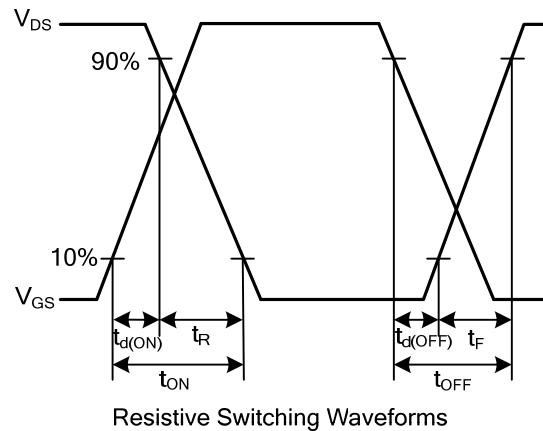
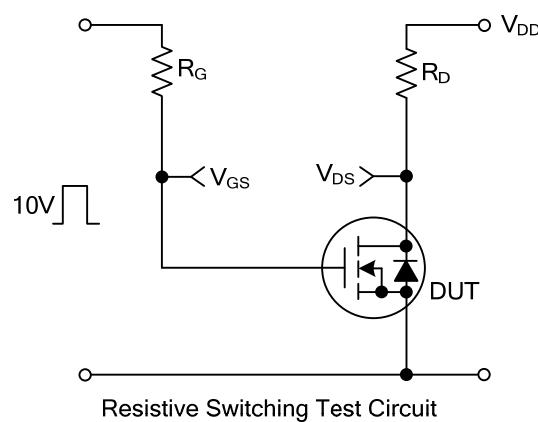
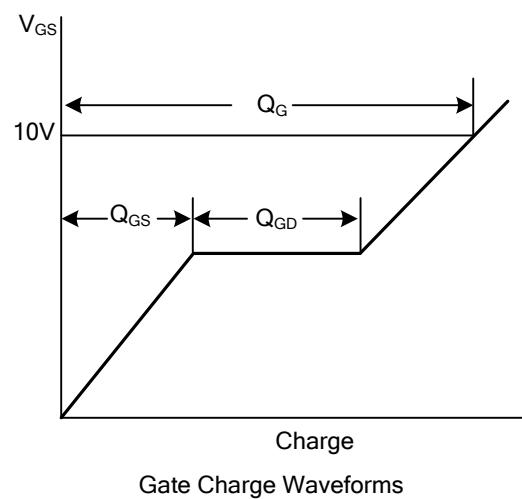
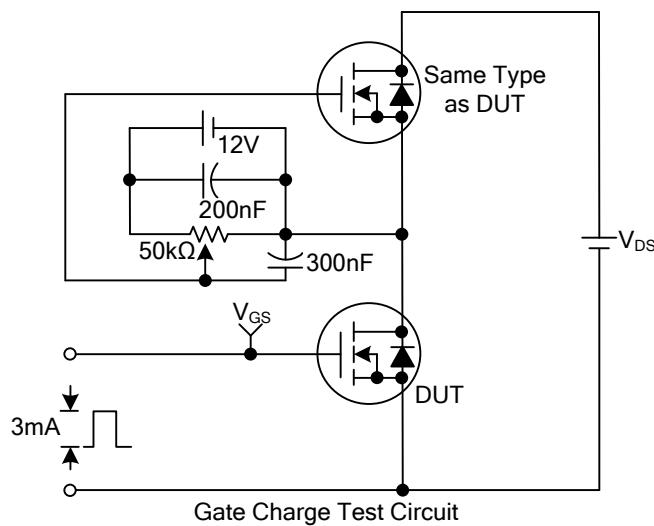
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

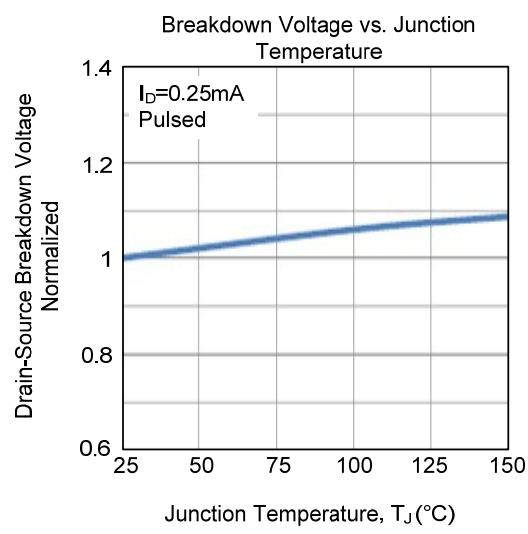
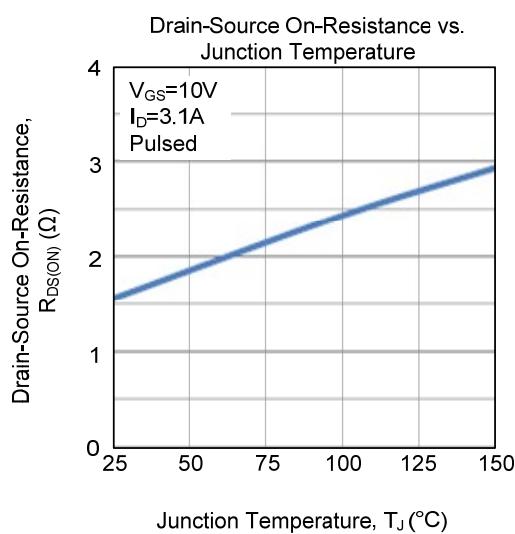
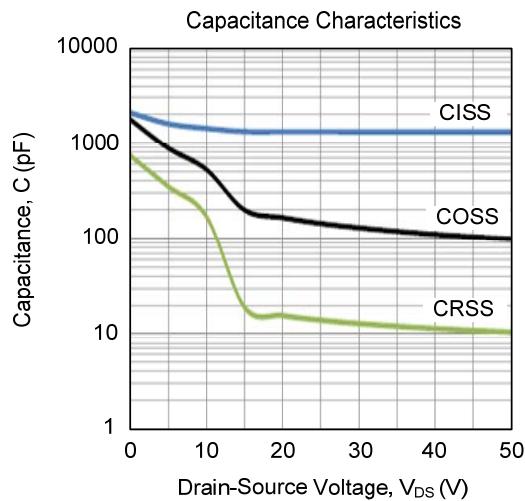
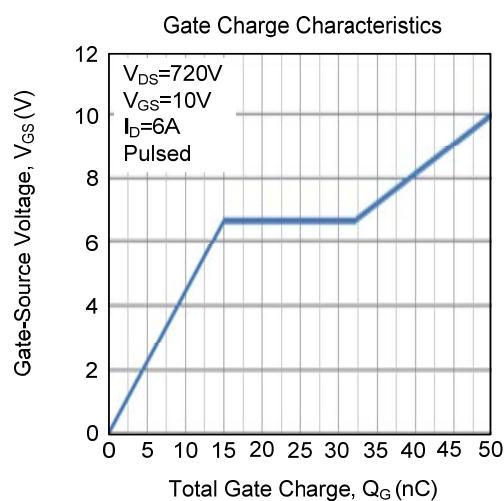
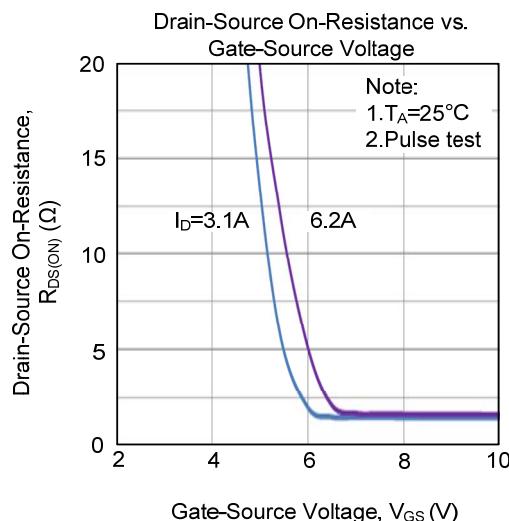
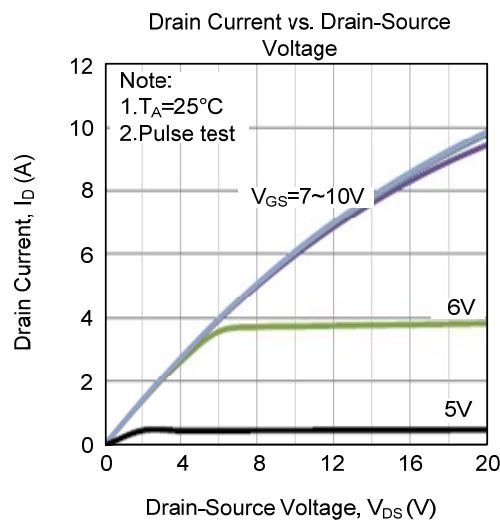
Peak Diode Recovery dv/dt Test Circuit & Waveforms



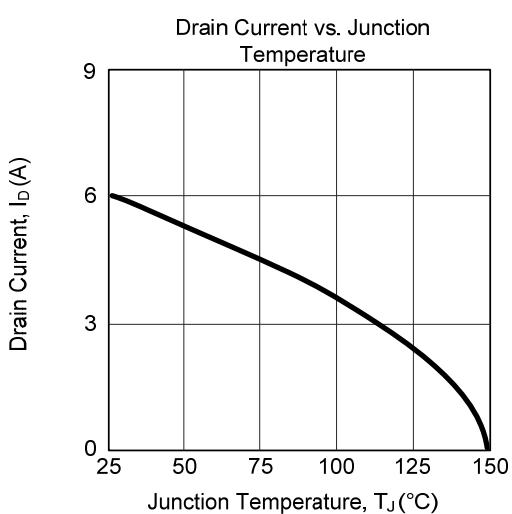
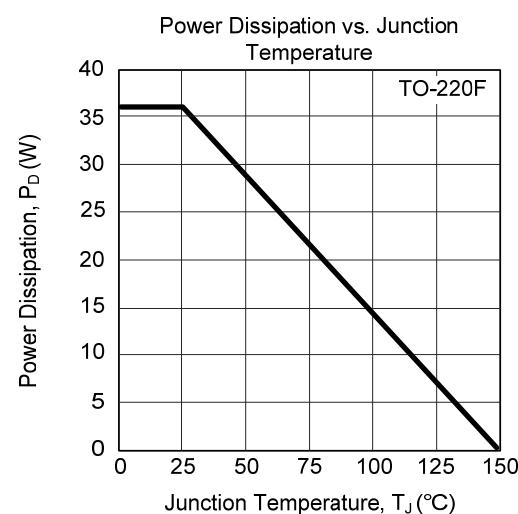
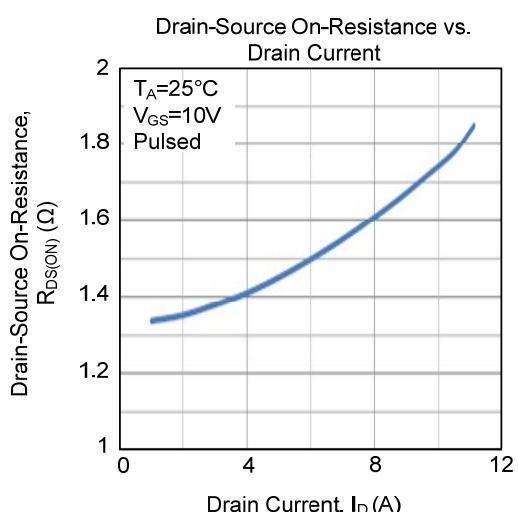
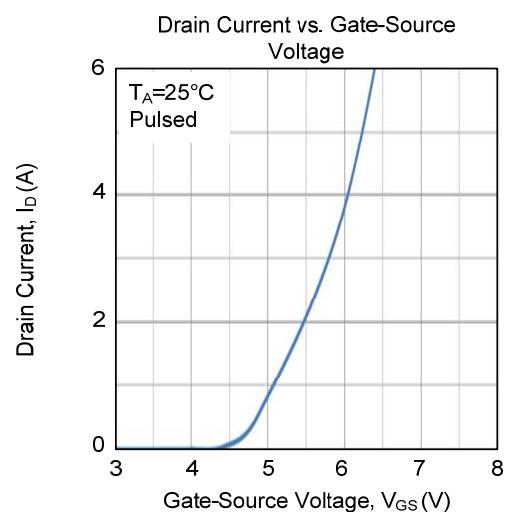
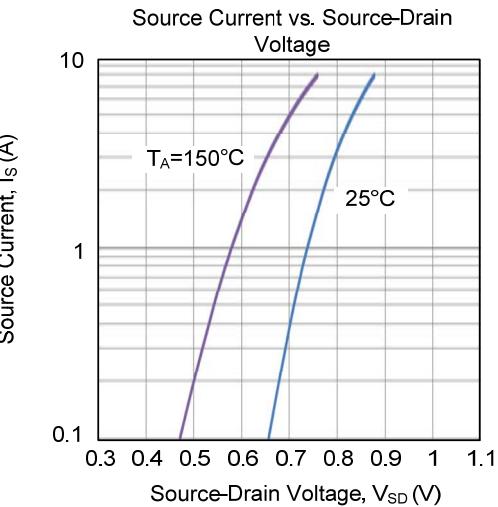
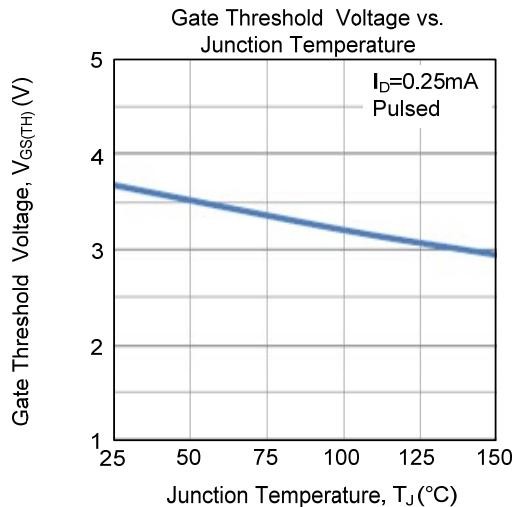
■ TEST CIRCUITS AND WAVEFORMS



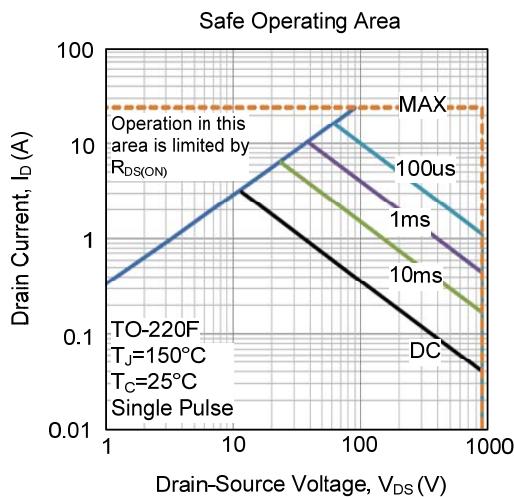
■ TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



- TYPICAL CHARACTERISTICS (Cont.)



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